



HVGT High voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

SHAPE DISPLAY:



FEATURES:

1. High reliability design.
2. High voltage design.
3. High frequency .
4. Conform to RoHS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. High voltage multiplier circuit
2. Electrostatic generator circuit .
3. General purpose high voltage rectifier.
4. Other.

MECHANICAL DATA:

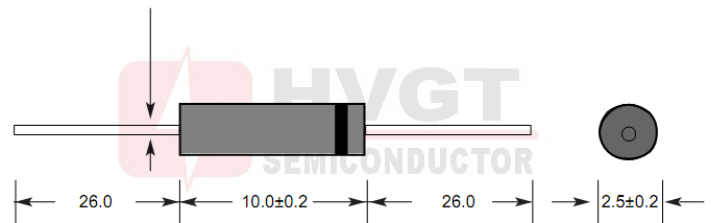
1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 0.28 grams (approx).

SIZE: (Unit:mm)

HVGT NAME: DO-210S

DO-210S Series

Lead Diameter 0.5±0.03



Unit:mm

MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_a=25^{\circ}C$;	12	kV
Average Output Current	I_F	$T_a=25^{\circ}C$;Resistive Load	5.0	mA
Surge Current	I_{FSM}	$T_a=25^{\circ}C$; 1/2 Sine(60Hz)	0.5	A
Junction Temperature	T_J		-40~+125	$^{\circ}C$
Allowable Operation Case Temperature	T_C		125	$^{\circ}C$
Storage Temperature	T_{STG}		-40~+125	$^{\circ}C$

ELECTRICAL CHARACTERISTICS: $T_a=25^{\circ}C$ (Unless otherwise specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_F	at $25^{\circ}C$; at $I_{F(AV)}$	45	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C$; at V_{RRM}	2.0	μA
	I_{R2}	at $100^{\circ}C$; at V_{RRM}	5.0	μA
Maximum Reverse Recovery Time	T_{RR}	at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$	80	nS
Junction Capacitance	C_J	at $25^{\circ}C$; $V_R=0V$; $f=1MHz$	1.0	pF



Fig1

Forward Characteristics

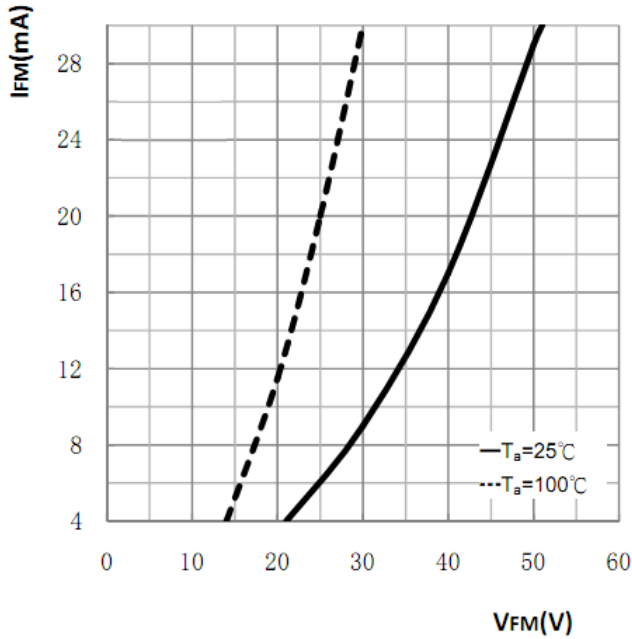


Fig2

Reverse Characteristics

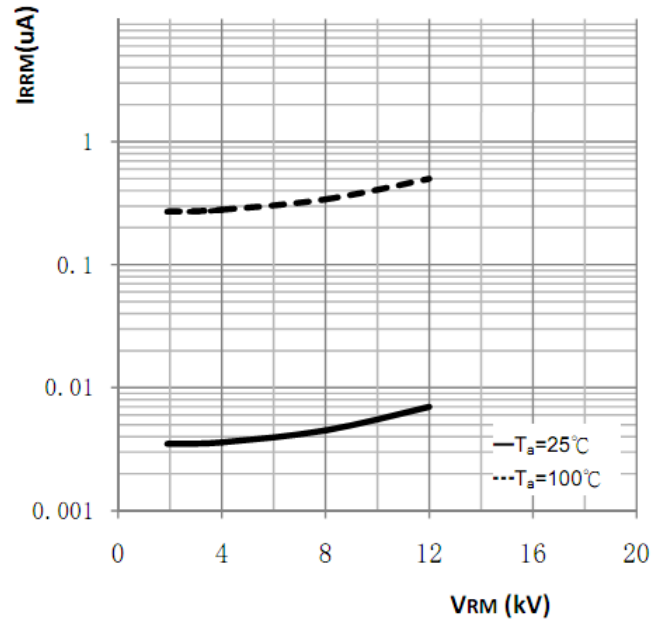


Fig3

V_R - I_F (AV) Curve

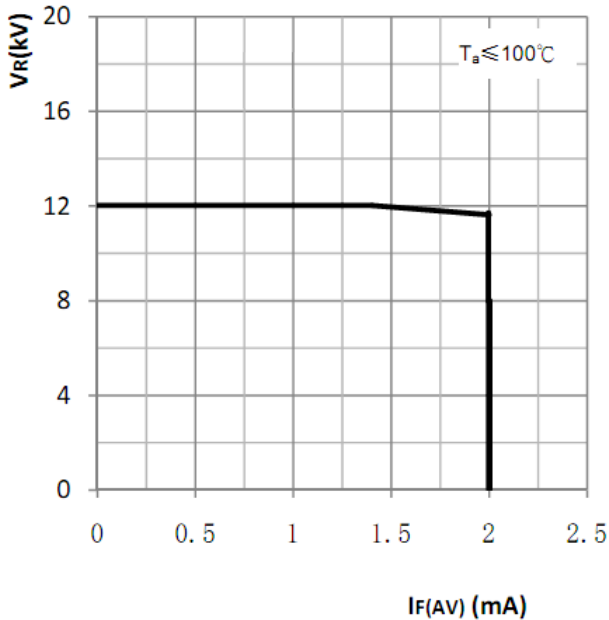
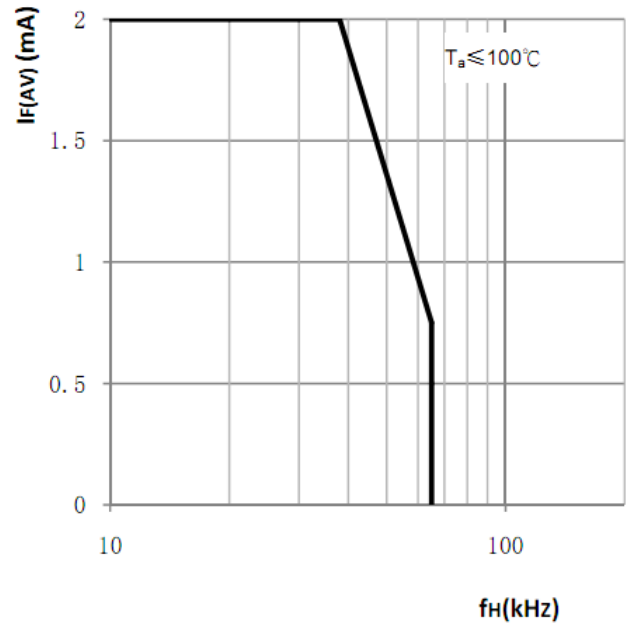


Fig4

I_F (AV)-fH Curve



Marking

Type

ESJA52-12A

Code

T73A

Cathode Mark

